

# MBR3045WT

Preferred Device

## SWITCHMODE™ Power Rectifier

... using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — Terminals 1 and 3 may be Connected for Parallel Operation at Full Rating
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Popular TO-247 Package

### Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 4.3 grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 30 units per plastic tube
- Marking: B3045

### MAXIMUM RATINGS

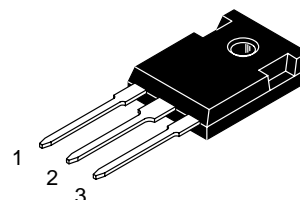
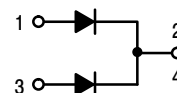
Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	45	V
Average Rectified Forward Current (Rated $V_R$ , $T_C = 105^\circ\text{C}$ ) Per Device Per Diode	$I_{F(AV)}$	30 15	A
Peak Repetitive Forward Current, (Rated $V_R$ , Square Wave, 20 kHz) Per Diode	$I_{FRM}$	30	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	200	A
Peak Repetitive Reverse Current (2.0 $\mu\text{s}$ , 1.0 kHz) Per Diode See Figure 6.	$I_{RRM}$	2.0	A
Storage Temperature Range	$T_{stg}$	-65 to +175	°C
Operating Junction Temperature	$T_J$	-65 to +150	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	°C
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$



ON Semiconductor™

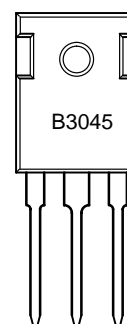
<http://onsemi.com>

## SCHOTTKY BARRIER RECTIFIER 30 AMPERES 45 VOLTS



TO-247  
CASE 340L  
PLASTIC

### MARKING DIAGRAM



B3045 = Device Code

### ORDERING INFORMATION

Device	Package	Shipping
MBR3045WT	TO-247	30 Units/Rail

Preferred devices are recommended choices for future use and best overall value.

# MBR3045WT

## THERMAL CHARACTERISTICS (Per Diode)

Rating	Symbol	Max	Unit
Thermal Resistance — Junction to Case	$R_{\theta JC}$	1.4	$^{\circ}C/W$
— Junction to Ambient	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS (Per Diode)

Instantaneous Forward Voltage (Note 1.) ( $i_F = 20$ Amps, $T_C = 125^{\circ}C$ ) ( $i_F = 30$ Amps, $T_C = 125^{\circ}C$ ) ( $i_F = 30$ Amps, $T_C = 25^{\circ}C$ )	$V_F$	0.6 0.72 0.76	Volts
Instantaneous Reverse Current (Note 1.) (Rated dc Voltage, $T_C = 125^{\circ}C$ ) (Rated dc Voltage, $T_C = 25^{\circ}C$ )	$i_R$	100 1.0	mA

1. Pulse Test: Pulse Width = 300  $\mu s$ , Duty Cycle  $\leq 2.0\%$ .

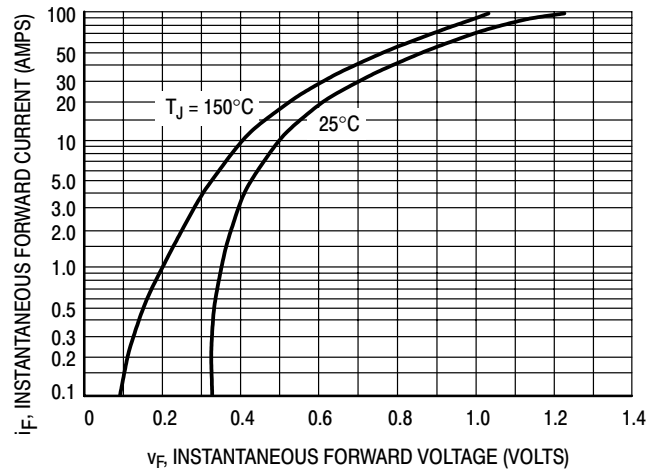


Figure 1. Typical Forward Voltage

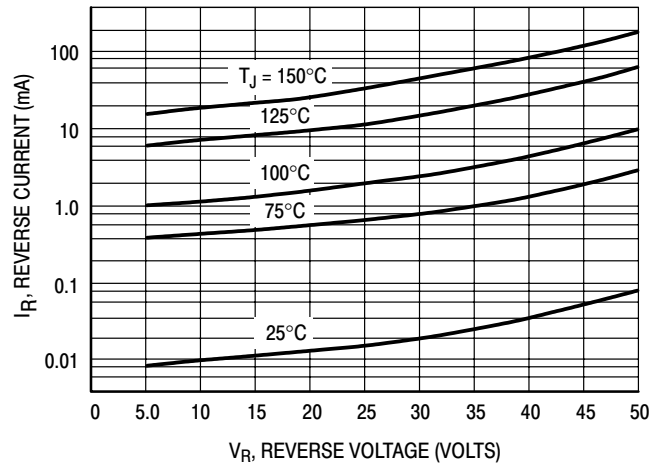


Figure 2. Typical Reverse Current

# MBR3045WT

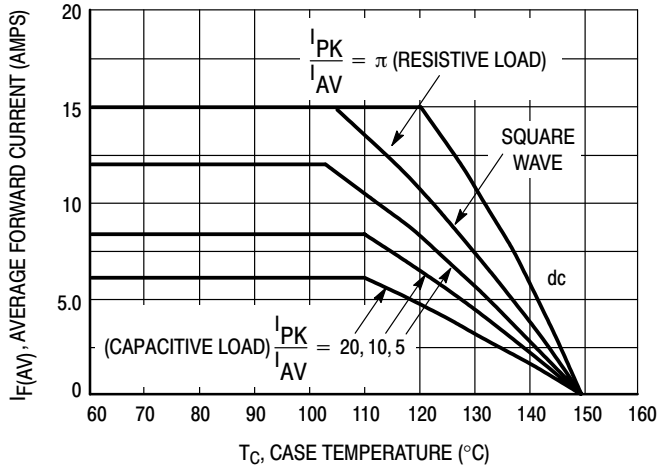


Figure 3. Current Derating (Per Leg)

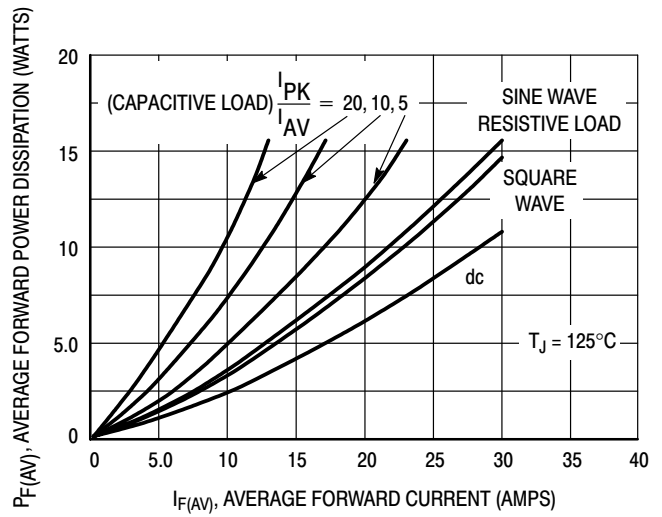


Figure 4. Forward Power Dissipation (Per Leg)

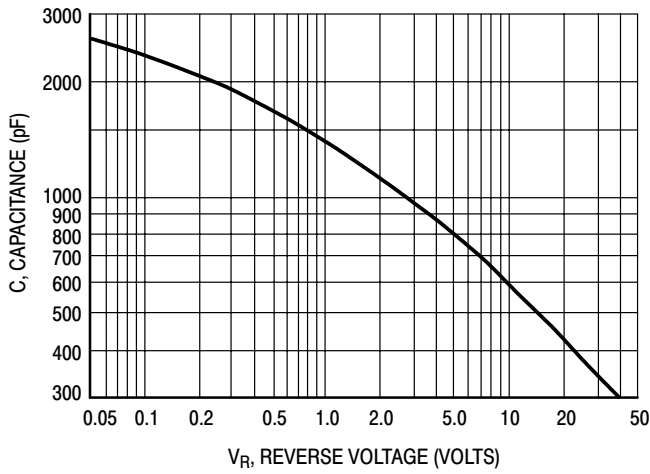


Figure 5. Capacitance

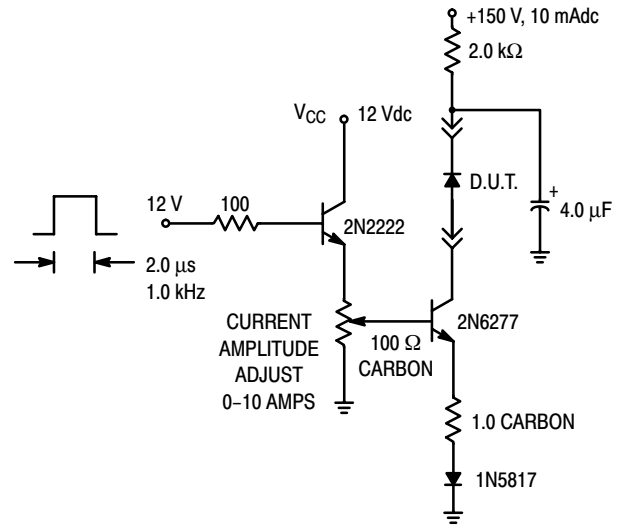


Figure 6. Test Circuit for Repetitive Reverse Current

